

Substitute for form 1449/PTO		Application Number	10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Filing Date	02/15/2005
(Use as many sheets as necessary)		Inventor(s)	James S. Im
		Art Unit	2822
		Examiner Name	Bac H. Au
		Attorney Docket Number	070050.2717

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	12.	5736709	4/7/1998	Neiheisel, Gary L.

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	63.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
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	78.	20050059265	3/17/2005	Im, James
	79.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
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	81.	20050142450	6/30/2005	Jung, Yun
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	86.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
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	88.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun
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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
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	96.	20070108472	5/17/2007	Jeong, Jae, Kyeong ; Shin, Hyun, Soo ; Kwon, Se, Yeoul ; Mo, Yeon, Gon
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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
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	James S. Im
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